National Semiconductor

March 1993

74ACQ241 • 54ACTQ/74ACTQ241 Quiet Series Octal Buffer/Line Driver with TRI-STATE® Outputs

General Description

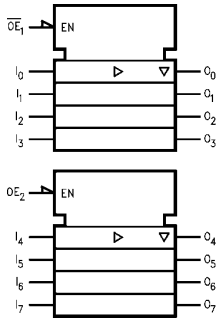
The 'ACQ/'ACTQ241 is an octal buffer and line driver designed to be employed as a memory address driver, clock driver and bus oriented transmitter or receiver which provides improved PC board density. The ACQ/ACTQ utilizes NSC Quiet Series technology to guarantee quiet output switching and improved dynamic threshold performance. FACT Quiet Series™ features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

Features

- I_{CC} and I_{OZ} reduced by 50%
- Guaranteed simultaneous switching noise level and dynamic threshold performance
- Guaranteed pin-to-pin skew AC performance
- Improved latch-up immunity
- TRI-STATE® outputs drive bus lines or buffer memory address registers
- Outputs source/sink 24 mA
- Faster prop delays than the standard 'AC/'ACT241
- 4 kV minimum ESD immunity ('ACTQ)
- Standard Military Drawing (SMD)
  — 'ACTQ241: 5962-92185

Logic Symbol

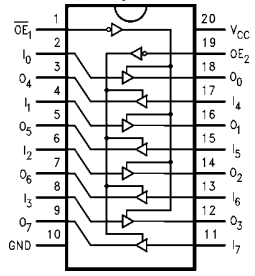
IEE/IEC



TL/F/10642–1

Connection Diagrams

Pin Assignment for DIP, Flatpak and SOIC



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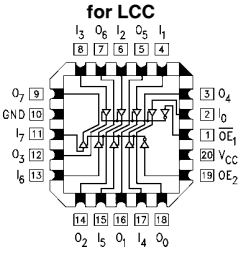
Pin Assignment for LCC



TL/F/10642–3

Pin Names	Description
$\overline{OE}_1$, OE_2	TRI-STATE Output Enable Inputs
I_0–I_7	Inputs
O_0–O_7	Outputs

Truth Tables

Inputs		Outputs (Pins 12, 14, 16, 18)
$\overline{OE}_1$	I_n	
L	L	L
L	H	H
H	X	Z

Inputs		Outputs (Pins 3, 5, 7, 9)
OE_2	I_n	
H	L	L
H	H	H
H	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance

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RRD-B30M75/Printed in U. S. A.

Absolute Maximum Rating (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5V to +7.0V
DC Input Diode Current (I_{IK})	
V_I = −0.5V	−20 mA
V_I = V_{CC} + 0.5V	+20 mA
DC Input Voltage (V_I)	−0.5V to V_{CC} + 0.5V
DC Output Diode Current (I_{OK})	
V_O = −0.5V	−20 mA
V_O = V_{CC} + 0.5V	+20 mA
DC Output Voltage (V_O)	−0.5V to V_{CC} + 0.5V
DC Output Source or Sink Current (I_O)	±50 mA
DC V_{CC} or Ground Current per Output Pin (I_{CC} or I_{GND})	±50 mA
Storage Temperature (T_{STG})	−65°C to +150°C
DC Latch-Up Source or Sink Current	±300 mA
Junction Temperature (T_J)	
CDIP	175°C
PDIP	140°C

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of FACT circuits outside databook specifications.

Recommended Operating Conditions

Supply Voltage (V_{CC})	
'ACQ	2.0V to 6.0V
'ACTQ	4.5V to 5.5V
Input Voltage (V_I)	0V to V_{CC}
Output Voltage (V_O)	0V to V_{CC}
Operating Temperature (T_A)	
74ACQ/ACTQ	−40°C to +85°C
54ACTQ	−55°C to +125°C
Minimum Input Edge Rate ΔV/Δt 'ACQ Devices V_{IN} from 30% to 70% of V_{CC} V_{CC} @ 3.0V, 4.5V, 5.5V	125 mV/ns
Minimum Input Edge Rate ΔV/Δt 'ACTQ Devices V_{IN} from 0.8V to 2.0V V_{CC} @ 4.5V, 5.5V	125 mV/ns

Note: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from −40°C to +125°C.

DC Electrical Characteristics for 'ACQ Family Devices

Symbol	Parameter	V_{CC} (V)	74ACQ T_A = +25°C	74ACQ T_A = −40°C to +85°C		Units	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	3.0	1.5	2.1	2.1	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	3.15	3.15		
		5.5	2.75	3.85	3.85		
V_{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.9	0.9	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	1.35	1.35		
		5.5	2.75	1.65	1.65		
V_{OH}	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9	V	I_{OUT} = −50 μA
		4.5	4.49	4.4	4.4		
		5.5	5.49	5.4	5.4		
		3.0		2.56	2.46	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −12 mA
		4.5		3.86	3.76		I_{OH} −24 mA
		5.5		4.86	4.76		−24 mA
V_{OL}	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1	V	I_{OUT} = 50 μA
		4.5	0.001	0.1	0.1		
		5.5	0.001	0.1	0.1		
		3.0		0.36	0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 12 mA
		4.5		0.36	0.44		I_{OL} 24 mA
		5.5		0.36	0.44		24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	μA	V_I = V_{CC}, GND (Note 1)

*All outputs loaded; thresholds on input associated with output under test.

DC Electrical Characteristics for 'ACQ Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74ACQ $T_A = +25°C$		74ACQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
I_{OLD}	†Minimum Dynamic Output Current	5.5			75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		4.0	40.0	μA	$V_{IN} = V_{CC}$ or GND (Note 1)
I_{OZ}	Maximum TRI-STATE Leakage Current	5.5		±0.25	±2.5	μA	V_I(OE) = V_{IL}, V_{IH} $V_I = V_{CC}$, GND $V_O = V_{CC}$, GND
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	5.0	1.1	1.5		V	*Figures 2-12, 13* (Notes 2, 3)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	5.0	−0.6	−1.2		V	*Figures 2-12, 13* (Notes 2, 3)
V_{IHD}	Minimum High Level Dynamic Input Voltage	5.0	3.1	3.5		V	(Notes 2, 4)
V_{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.9	1.5		V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{IN} and I_{CC} @ 3.0V are guaranteed to be less than or equal to the respective limit @ 5.5V V_{CC}.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). Data Inputs are driven 0V to 5V. One output @ GND.

Note 4: Max number of Data Inputs (n) switching. n−1 Inputs switching 0V to 5V ('ACQ). Input-under-test switching: 5V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f = 1 MHz.

DC Electrical Characteristics for 'ACTQ Family Devices

Symbol	Parameter	V_{CC} (V)	74ACTQ $T_A = +25°C$	54ACTQ $T_A = -55°C$ to $+125°C$	74ACTQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I_{OUT} = −50 μA
		4.5 5.5		3.86 4.86	3.70 4.70	3.76 4.76	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −24 mA −24 mA
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	0.1 0.1	V	I_{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.50 0.50	0.44 0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 24 mA 24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	±1.0	μA	$V_I = V_{CC}$, GND

*All outputs loaded; thresholds on input associated with output under test.

DC Electrical Characteristics for 'ACTQ Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74ACTQ $T_A = +25°C$		54ACTQ $T_A = -55°C$ to $+125°C$	74ACTQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits				
I_{OZ}	Maximum TRI-STATE Leakage Current	5.5		±0.25	±5.0	±2.5	μA	$V_I = V_{IL}, V_{IH}$ $V_O = V_{CC}$, GND
I_{CCT}	Maximum I_{CC}/Input	5.5	0.6		1.6	1.5	mA	$V_I = V_{CC} - 2.1V$
I_{OLD}	†Minimum Dynamic Output Current	5.5			50	75	mA	$V_{OLD} = 1.65V$ Max
I_{OHD}		5.5			−50	−75	mA	$V_{OHD} = 3.85V$ Min
I_{CC}	Maximum Quiescent Supply Current	5.5		4.0	80.0	40.0	μA	$V_{IN} = V_{CC}$ or GND (Note 1)
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	5.0	1.1	1.5			V	*Figures 2-12, 13* (Notes 2, 3)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	5.0	−0.6	−1.2			V	*Figures 2-12, 13* (Notes 2, 3)
V_{IHD}	Minimum High Level Dynamic Input Voltage	5.0	1.9	2.2			V	(Notes 2, 4)
V_{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.2	0.8			V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{CC} for 54ACTQ @ 25°C is identical to 74ACTQ @ 25°C.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). Data Inputs are driven 0V to 3V. One output @ GND.

Note 4: Max number of Data Inputs (n) switching. n−1 Inputs switching 0V to 3V ('ACTQ). Input-under-test switching: 3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f = 1 MHz.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACQ $T_A = +25°C$, $C_L = 50$ pF			74ACQ $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	
t_{PHL}, t_{PLH}	Propagation Delay Data to Output	3.3 5.0	2.0 1.5	6.5 4.5	9.0 6.0	2.0 1.5	9.5 6.5	ns
t_{PZL}, t_{PZH}	Output Enable Time	3.3 5.0	2.5 1.5	8.0 5.5	13.0 8.5	2.5 1.5	13.5 9.0	ns
t_{PHZ}, t_{PLZ}	Output Disable Time	3.3 5.0	1.0 1.0	8.5 5.5	14.5 9.5	1.0 1.0	15.0 10.0	ns
t_{OSHL}, t_{OSLH}	Output to Output Skew **Data to Output	3.3 5.0		1.0 0.5	1.5 1.0		1.5 1.0	ns

*Voltage Range 5.0 is 5.0V ±0.5V.
Voltage Range 3.3 is 3.3V ±0.3V.

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACTQ			54ACTQ		74ACTQ		Units
			$T_A = +25°C$, $C_L = 50$ pF			$T_A = -55°C$ to $+125°C$, $C_L = 50$ pF		$T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		
			Min	Typ	Max	Min	Max	Min	Max	
t_{PHL}, t_{PLH}	Propagation Delay Data to Output	5.0	1.5	5.0	6.5	1.5	8.0	1.5	7.0	ns
t_{PZL}, t_{PZH}	Output Enable Time	5.0	1.5	6.5	9.0	1.5	10.5	1.5	9.5	ns
t_{PHZ}, t_{PLZ}	Output Disable Time	5.0	1.0	7.0	10.0	1.5	9.5	1.0	10.5	ns
t_{OSHL}, t_{OSLH}	Output to Output Skew **Data to Output	5.0		0.5	1.0				1.0	ns

*Voltage Range 5.0 is 5.0V ±0.5V.

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

Capacitance

Symbol	Parameter	Typ	Units	Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = OPEN
C_{PD}	Power Dissipation Capacitance	70	pF	V_{CC} = 5.0V

FACT Noise Characteristics

The setup of a noise characteristics measurement is critical to the accuracy and repeatability of the tests. The following is a brief description of the setup used to measure the noise characteristics of FACT.

Equipment:

Hewlett Packard Model 8180A Word Generator
PC-163A Test Fixture
Tektronics Model 7854 Oscilloscope

Procedure:

1. Verify Test Fixture Loading: Standard Load 50 pF, 500Ω.
2. Deskew the word generator so that no two channels have greater than 150 ps skew between them. This requires that the oscilloscope be deskewed first. Swap out the channels that have more than 150 ps of skew until all channels being used are within 150 ps. It is important to deskew the word generator channels before testing. This will ensure that the outputs switch simultaneously.
3. Terminate all inputs and outputs to ensure proper loading of the outputs and that the input levels are at the correct voltage.
4. Set V_{CC} to 5.0V.
5. Set the word generator to toggle all but one output at a frequency of 1 MHz. Greater frequencies will increase DUT heating and affect the results of the measurement.
6. Set the word generator input levels at 0V LOW and 3V HIGH for ACT devices and 0V LOW and 5V HIGH for AC devices. Verify levels with a digital volt meter.

V_{OLP}/V_{OLV} and V_{OHP}/V_{OHV}:

- Determine the quiet output pin that demonstrates the greatest noise levels. The worst case pin will usually be the furthest from the ground pin. Monitor the output voltages using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- Measure V_{OLP} and V_{OLV} on the quiet output during the HL transition. Measure V_{OHP} and V_{OHV} on the quiet output during the LH transition.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

V_{ILD} and V_{IHD}:

- Monitor one of the switching outputs using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- First increase the input LOW voltage level, V_{IL}, until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input LOW voltage level at which oscillation occurs is defined as V_{ILD}.
- Next increase the input HIGH voltage level on the word generator, V_{IH} until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input HIGH voltage level at which oscillation occurs is defined as V_{IHD}.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

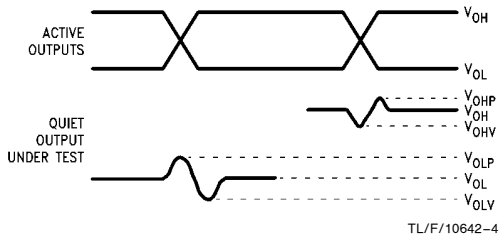


FIGURE 1. Quiet Output Noise Voltage Waveforms

Note A. V_{OHV} and V_{OLP} are measured with respect to ground reference.

Note B. Input pulses have the following characteristics: f = 1 MHz, t_r = 3 ns, t_f = 3 ns, skew < 150 ps.

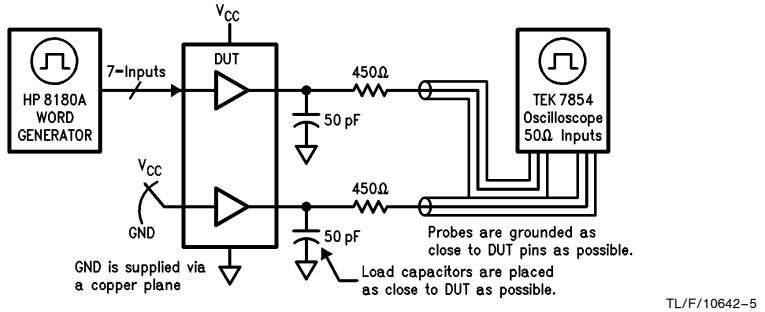


FIGURE 2. Simultaneous Switching Test Circuit

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

74ACTQ 241 P C QR

Temperature Range Family
- 74ACQ = Commercial
- 74ACTQ = Commercial TTL-Compatible
- 54ACTQ = Military TTL-Compatible

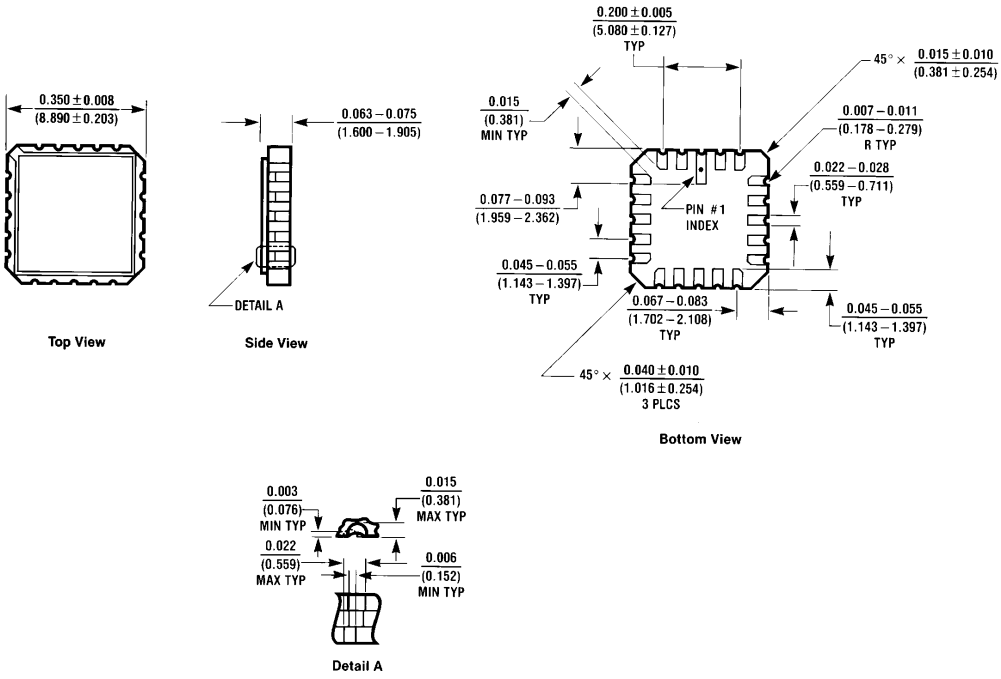
Device Type

Package Code
- P = Plastic DIP
- D = Ceramic DIP
- F = Flatpak
- S = Small Outline Package (SOIC)

Special Variations
- X = Devices shipped in 13″ reels
- QR = Commercial grade device with burn-in
- QB = Military grade device with environmental and burn-in processing shipped in tubes

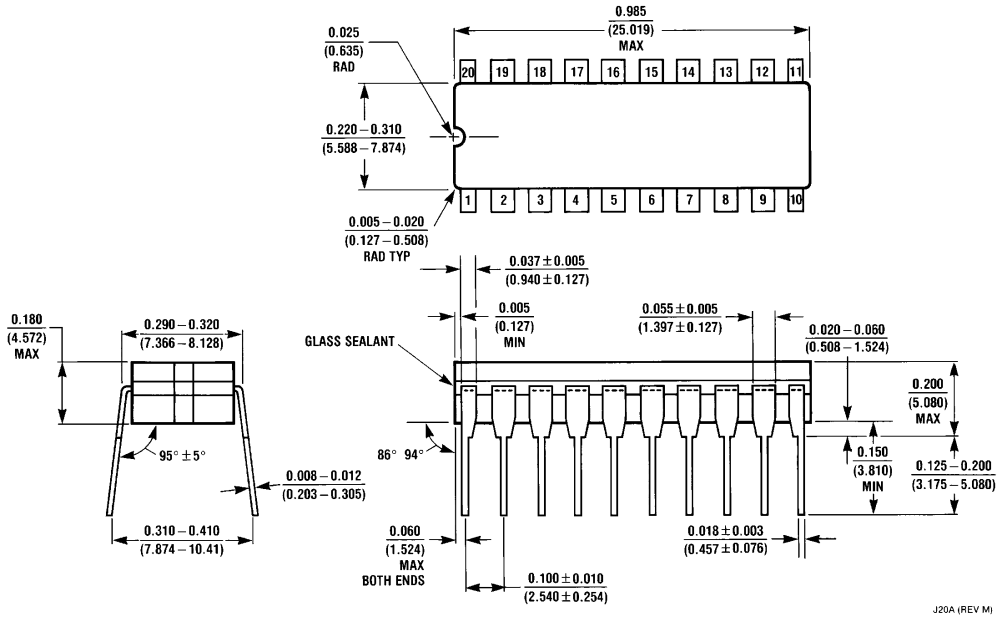
Temperature Range
- C = Commercial (−40°C to +85°C)
- M = Military (−55°C to +125°C)

Physical Dimensions inches (millimeters)

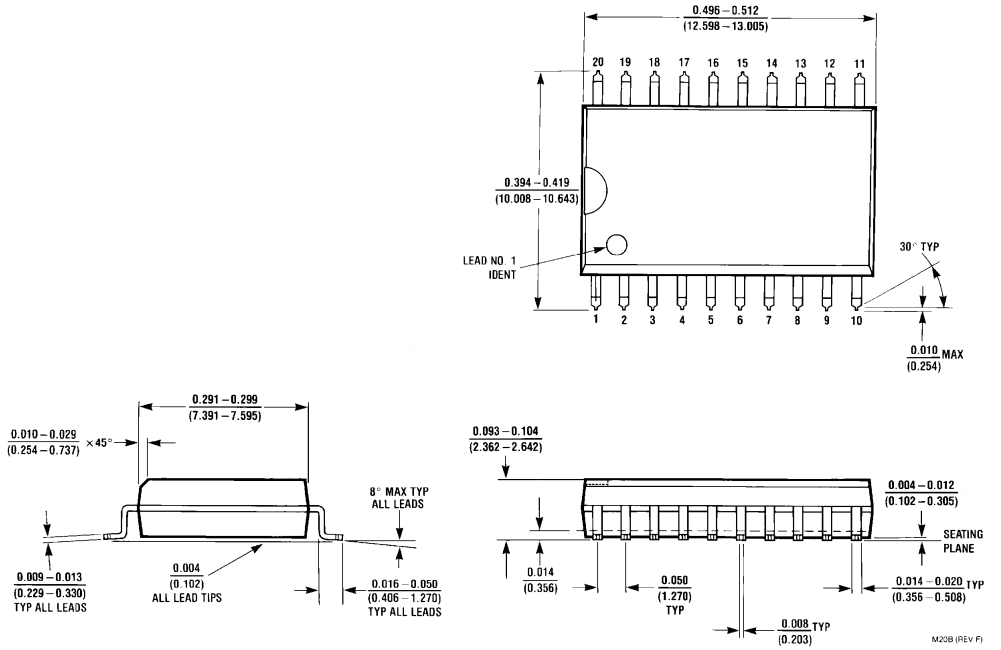


20-Terminal Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

Physical Dimensions inches (millimeters) (Continued)

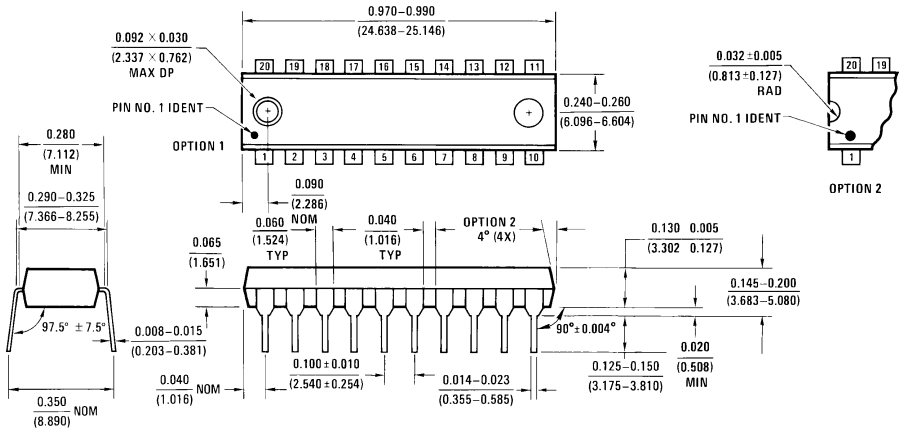


20-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J20A



20-Lead Small Outline Integrated Circuit (S)
NS Package Number M20B

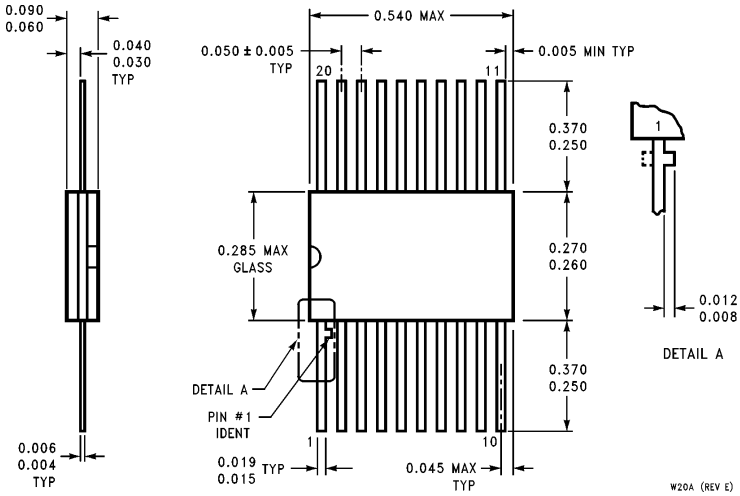
Physical Dimensions inches (millimeters) (Continued)



20-Lead Plastic Dual-In-Line Package (P)
NS Package Number N20B

Physical Dimensions inches (millimeters) (Continued)

Lit. # 114662



20-Lead Ceramic Flatpak (F)
NS Package Number W20A

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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